

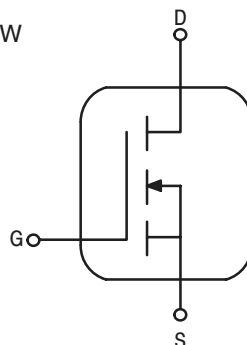
The RF MOSFET Line

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for Class A–AB common source, linear power amplifiers in the 960 MHz range. The MRF6522–10R1 has been specifically designed for use in Communications Network (GSM) base stations. The package offers the advantage of SMD.

- Specified 26 Volts, 960 MHz, Class AB Characteristics
Output Power = 10 Watts CW
Power Gain = 15 dB Min @ 960 MHz, 10 Watts CW
Drain Efficiency = 48% Min @ 960 MHz, 10 Watts CW
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- S-Parameter Characterization at High Bias Levels
- Bottom Side Source Eliminates DC Isolators, Reducing Common Mode Inductances
- In Tape and Reel. R1 Suffix = 500 Units per 12 mm. 7 inch Reel.



MRF6522-10R1

**960 MHz, 10 W, 26 V
LATERAL N-CHANNEL
RF POWER MOSFET**



CASE 458C-03, STYLE 1
NI-200Z

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Source Voltage	V _{DSS}	65	Vdc
Gate–Source Voltage	V _{GS}	±20	Vdc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	29 0.17	Watts W/°C
Storage Temperature Range	T _{stg}	–65 to +150	°C
Operating Junction Temperature	T _J	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (1)	$R_{\theta JC}$	4.0	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain–Source Breakdown Voltage ($V_{GS} = 0$ Vdc, $I_D = 0.2$ mA)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 26$ Vdc, $V_{GS} = 0$ Vdc)	I_{DSS}	—	—	1.0	μ Adc
Gate–Source Leakage Current ($V_{GS} = 20$ Vdc, $V_{DS} = 0$ Vdc)	I_{GSS}	—	—	1.0	μ Adc

(1) Thermal resistance is determined under specified RF operating condition.

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

ELECTRICAL CHARACTERISTICS continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = 10\text{ V}$, $I_D = 50\text{ }\mu\text{A}$)	$V_{GS(th)}$	1.25	3.0	4.0	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 100\text{ mA}$)	$V_{GS(Q)}$	2.25	4.0	5.0	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ A}$)	$V_{DS(on)}$	—	—	0.9	Vdc

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 26\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{iss}	—	17	—	pF
Output Capacitance ($V_{DS} = 26\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{oss}	—	10	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{rss}	—	0.9	—	pF

FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system)

Common–Source Power Gain ($V_{DS} = 26\text{ V}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 100\text{ mA}$, $f = 960\text{ MHz}$)	G_{ps}	15	17	—	dB
Drain Efficiency ($V_{DS} = 26\text{ V}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 100\text{ mA}$, $f = 960\text{ MHz}$)	η	48	50	—	%
Input Return Loss ($V_{DS} = 26\text{ V}$, $P_{out} = 10\text{ W CW}$, $I_{DQ} = 100\text{ mA}$, $f = 960\text{ MHz}$)	IRL	—	—	–9	dB

TYPICAL CHARACTERISTICS

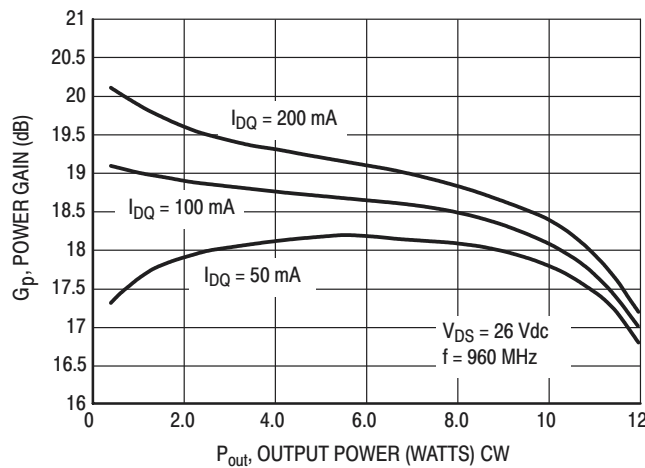


Figure 1. Power Gain versus Output Power

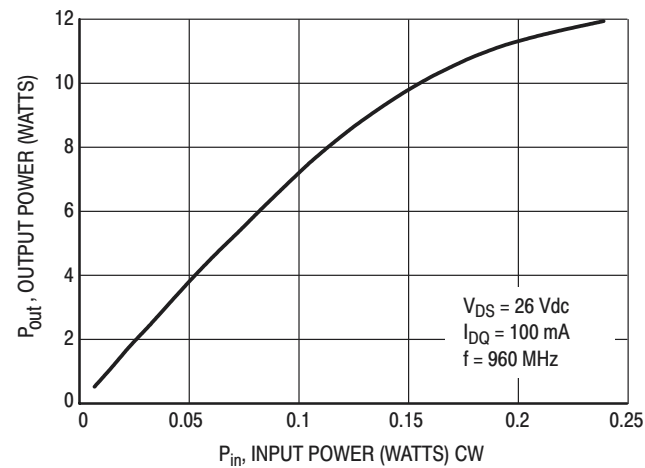


Figure 2. Output Power versus Input Power

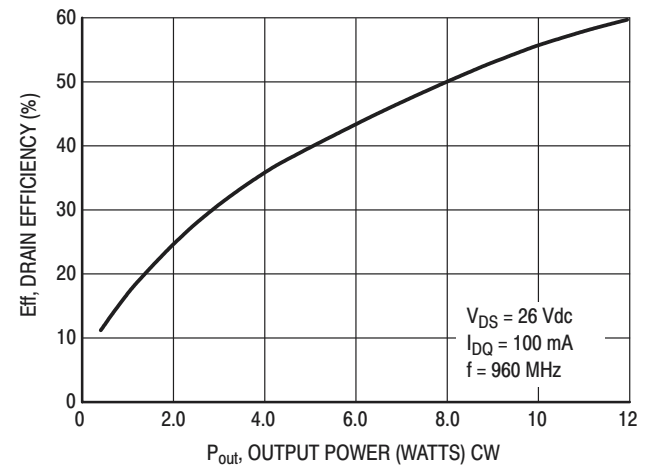


Figure 3. Drain Efficiency versus Output Power

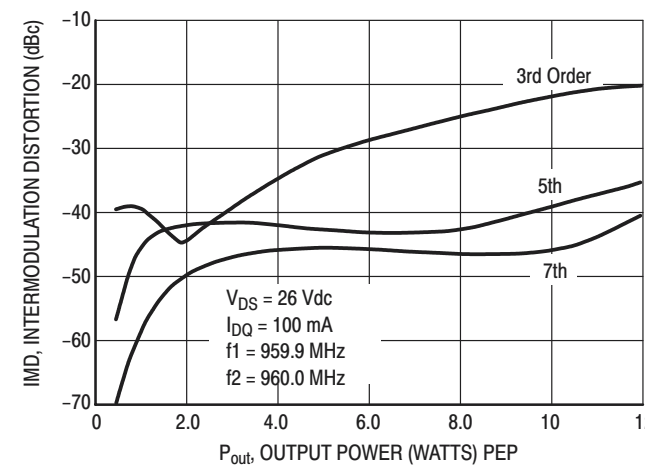
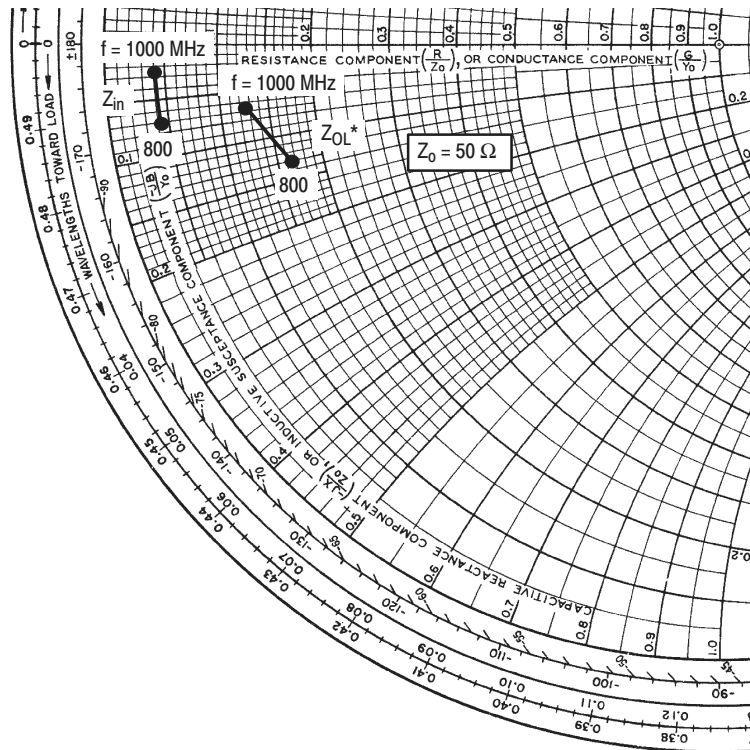


Figure 4. Intermodulation Distortion Products versus Output Power



f MHz	Z_{in} Ohms	Z_{OL}^* Ohms
800	$2.20 - j3.00$	$8.50 - j6.20$
825	$2.20 - j2.80$	$8.43 - j6.15$
850	$2.20 - j2.60$	$8.35 - j6.10$
875	$2.20 - j2.40$	$8.28 - j6.08$
900	$2.20 - j2.20$	$8.20 - j6.05$
925	$2.19 - j1.86$	$7.95 - j5.70$
950	$2.13 - j1.68$	$7.50 - j4.75$
975	$2.03 - j1.45$	$6.90 - j3.58$
1000	$2.00 - j1.00$	$6.50 - j3.00$

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the optimum load impedance into which the device operates at a given output power, voltage, current and frequency.

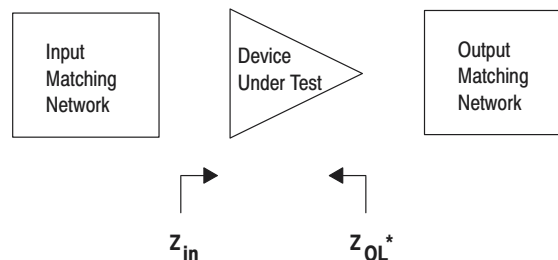


Figure 5. Series Equivalent Input and Output Impedance

Table 1. Common Source S-Parameters at $V_{DS} = 12$ Vdc, $I_D = 100$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.794	-158	2.77	54	0.050	-29	0.720	-150
0.525	0.800	-159	2.61	52	0.049	-32	0.730	-151
0.550	0.807	-160	2.45	49	0.048	-33	0.738	-152
0.575	0.811	-161	2.31	48	0.047	-35	0.746	-153
0.600	0.816	-162	2.18	46	0.046	-37	0.755	-154
0.625	0.822	-163	2.06	44	0.045	-38	0.763	-155
0.650	0.826	-164	1.95	42	0.043	-40	0.770	-156
0.675	0.832	-165	1.85	40	0.042	-41	0.779	-157
0.700	0.836	-166	1.75	39	0.041	-41	0.785	-158
0.725	0.841	-166	1.66	37	0.040	-42	0.793	-159
0.750	0.846	-167	1.58	35	0.039	-44	0.800	-160
0.775	0.851	-168	1.51	34	0.038	-45	0.805	-161
0.800	0.855	-168	1.44	32	0.037	-46	0.812	-162
0.825	0.858	-169	1.37	31	0.036	-47	0.818	-163
0.850	0.863	-170	1.31	29	0.035	-48	0.824	-164
0.875	0.866	-171	1.25	28	0.034	-49	0.830	-165
0.900	0.869	-172	1.20	27	0.033	-50	0.835	-166
0.925	0.872	-172	1.15	25	0.031	-51	0.840	-166
0.950	0.876	-173	1.10	24	0.030	-52	0.846	-167
0.975	0.879	-174	1.06	23	0.029	-52	0.850	-168
1.000	0.882	-174	1.02	22	0.028	-53	0.853	-169

Table 2. Common Source S-Parameters at $V_{DS} = 12$ Vdc, $I_D = 250$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.784	-164	3.49	59	0.041	-22	0.690	-158
0.525	0.789	-165	3.29	57	0.040	-25	0.697	-159
0.550	0.794	-166	3.11	55	0.040	-26	0.705	-160
0.575	0.798	-167	2.94	53	0.038	-26	0.711	-160
0.600	0.802	-167	2.79	51	0.037	-28	0.719	-161
0.625	0.806	-168	2.65	50	0.037	-30	0.726	-162
0.650	0.811	-169	2.52	48	0.036	-31	0.732	-162
0.675	0.814	-169	2.40	46	0.035	-32	0.740	-163
0.700	0.819	-170	2.28	45	0.034	-32	0.747	-164
0.725	0.823	-171	2.18	43	0.034	-34	0.753	-164
0.750	0.827	-171	2.08	42	0.032	-36	0.760	-165
0.775	0.831	-172	1.99	40	0.032	-36	0.765	-166
0.800	0.834	-172	1.90	39	0.031	-36	0.772	-166
0.825	0.838	-173	1.82	37	0.031	-38	0.778	-167
0.850	0.842	-174	1.74	36	0.029	-38	0.783	-168
0.875	0.845	-174	1.67	35	0.028	-39	0.790	-169
0.900	0.850	-175	1.61	33	0.028	-39	0.797	-169
0.925	0.852	-175	1.54	32	0.027	-41	0.801	-170
0.950	0.854	-176	1.48	31	0.027	-42	0.807	-170
0.975	0.859	-176	1.43	30	0.025	-41	0.810	-171
1.000	0.861	-177	1.38	28	0.025	-42	0.815	-171

Table 3. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 100$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.832	-155	4.05	56	0.033	-25	0.687	-135
0.525	0.836	-156	3.81	54	0.033	-27	0.697	-137
0.550	0.841	-157	3.58	51	0.034	-28	0.707	-138
0.575	0.845	-159	3.38	49	0.032	-31	0.718	-140
0.600	0.849	-160	3.19	47	0.031	-32	0.728	-141
0.625	0.853	-161	3.02	45	0.030	-34	0.737	-143
0.650	0.856	-162	2.86	43	0.029	-35	0.746	-144
0.675	0.861	-163	2.71	42	0.028	-37	0.755	-145
0.700	0.865	-164	2.57	40	0.028	-37	0.762	-147
0.725	0.868	-165	2.44	38	0.026	-38	0.771	-148
0.750	0.871	-166	2.32	37	0.025	-40	0.779	-149
0.775	0.875	-166	2.21	35	0.025	-41	0.786	-150
0.800	0.877	-167	2.11	33	0.023	-41	0.793	-151
0.825	0.880	-168	2.02	32	0.022	-43	0.800	-152
0.850	0.884	-169	1.92	30	0.022	-43	0.808	-154
0.875	0.886	-170	1.84	29	0.021	-44	0.815	-155
0.900	0.889	-171	1.76	27	0.020	-43	0.820	-156
0.925	0.892	-171	1.68	26	0.020	-46	0.826	-157
0.950	0.894	-172	1.61	24	0.019	-45	0.832	-158
0.975	0.897	-173	1.55	23	0.018	-47	0.837	-159
1.000	0.899	-173	1.49	22	0.017	-48	0.842	-160

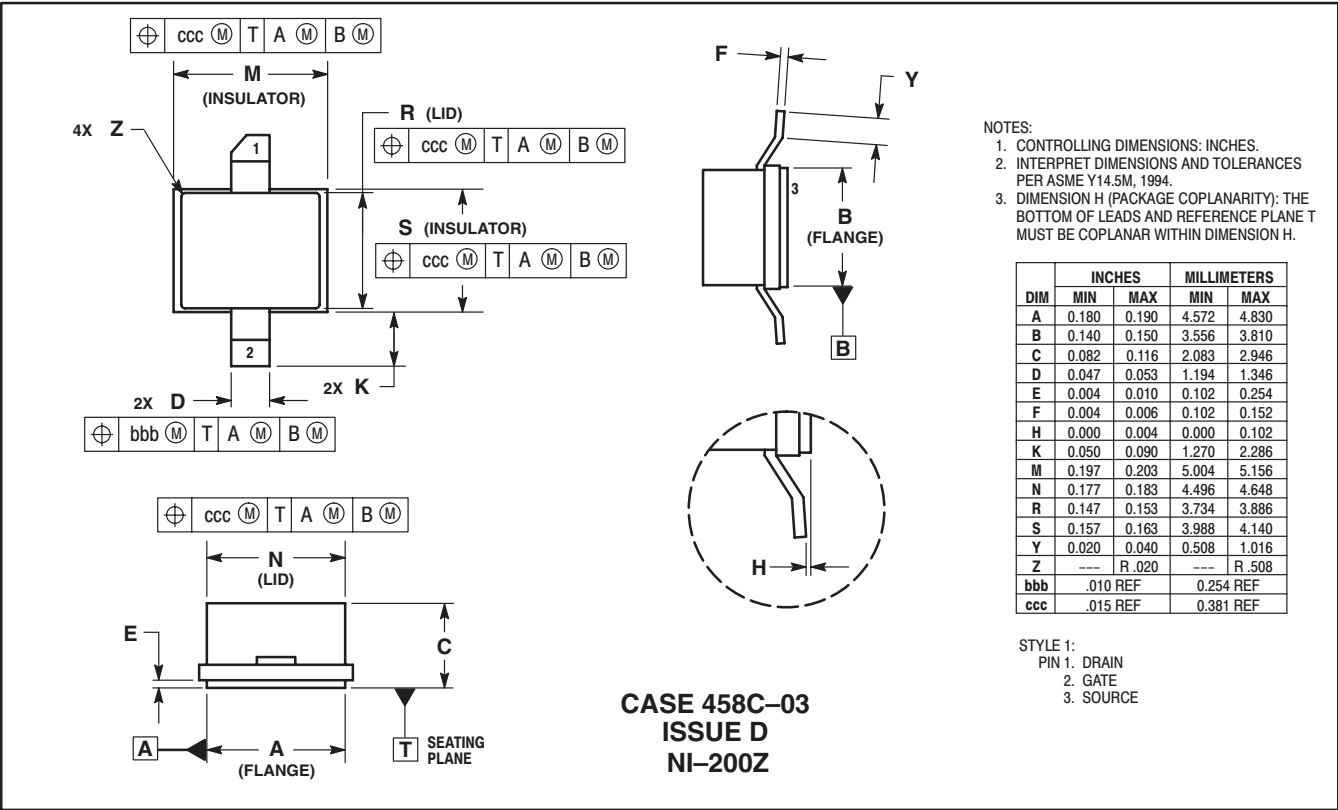
Table 4. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 250$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.824	-160	5.02	59	0.029	-21	0.627	-143
0.525	0.828	-161	4.74	57	0.027	-22	0.638	-144
0.550	0.832	-162	4.47	55	0.026	-22	0.648	-145
0.575	0.835	-163	4.23	53	0.027	-24	0.658	-146
0.600	0.838	-164	4.01	51	0.025	-26	0.669	-147
0.625	0.842	-165	3.81	50	0.025	-26	0.678	-148
0.650	0.844	-166	3.61	48	0.024	-25	0.687	-150
0.675	0.848	-167	3.43	46	0.023	-28	0.697	-150
0.700	0.851	-168	3.27	44	0.023	-30	0.706	-151
0.725	0.855	-168	3.12	43	0.022	-30	0.714	-152
0.750	0.858	-169	2.97	41	0.021	-31	0.723	-153
0.775	0.861	-170	2.84	39	0.021	-31	0.731	-154
0.800	0.863	-170	2.72	38	0.020	-32	0.738	-155
0.825	0.866	-171	2.60	36	0.019	-33	0.746	-156
0.850	0.870	-172	2.49	35	0.018	-34	0.754	-157
0.875	0.871	-173	2.38	33	0.018	-34	0.763	-158
0.900	0.875	-173	2.29	32	0.017	-35	0.768	-159
0.925	0.877	-174	2.20	30	0.016	-36	0.776	-160
0.950	0.879	-175	2.11	29	0.016	-36	0.782	-161
0.975	0.883	-175	2.03	28	0.016	-34	0.787	-161
1.000	0.885	-176	1.95	27	0.015	-34	0.793	-162

Table 5. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 500$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.500	0.832	-162	5.08	60	0.025	-17	0.612	-145
0.525	0.834	-162	4.80	58	0.025	-20	0.624	-146
0.550	0.838	-164	4.53	56	0.024	-21	0.635	-147
0.575	0.840	-164	4.29	54	0.024	-21	0.644	-148
0.600	0.844	-165	4.07	52	0.023	-23	0.655	-149
0.625	0.847	-166	3.86	50	0.023	-24	0.664	-150
0.650	0.849	-167	3.66	48	0.022	-25	0.673	-151
0.675	0.852	-168	3.48	46	0.021	-27	0.682	-152
0.700	0.856	-169	3.32	45	0.021	-28	0.690	-153
0.725	0.858	-170	3.17	43	0.020	-28	0.701	-154
0.750	0.861	-170	3.02	41	0.019	-30	0.709	-154
0.775	0.864	-171	2.89	40	0.019	-29	0.716	-155
0.800	0.866	-172	2.76	38	0.018	-29	0.723	-156
0.825	0.869	-172	2.65	37	0.017	-29	0.733	-157
0.850	0.872	-173	2.53	35	0.017	-31	0.742	-158
0.875	0.874	-174	2.43	34	0.016	-31	0.751	-159
0.900	0.878	-175	2.33	32	0.015	-31	0.757	-160
0.925	0.879	-175	2.24	31	0.015	-32	0.763	-161
0.950	0.881	-176	2.15	29	0.014	-31	0.770	-161
0.975	0.884	-176	2.07	28	0.014	-31	0.775	-162
1.000	0.886	-177	2.00	27	0.013	-30	0.781	-163

PACKAGE DIMENSIONS



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